

Supplementary Information

CuInS₂ quantum dots-based unipolar resistive switching for non-volatile memory application

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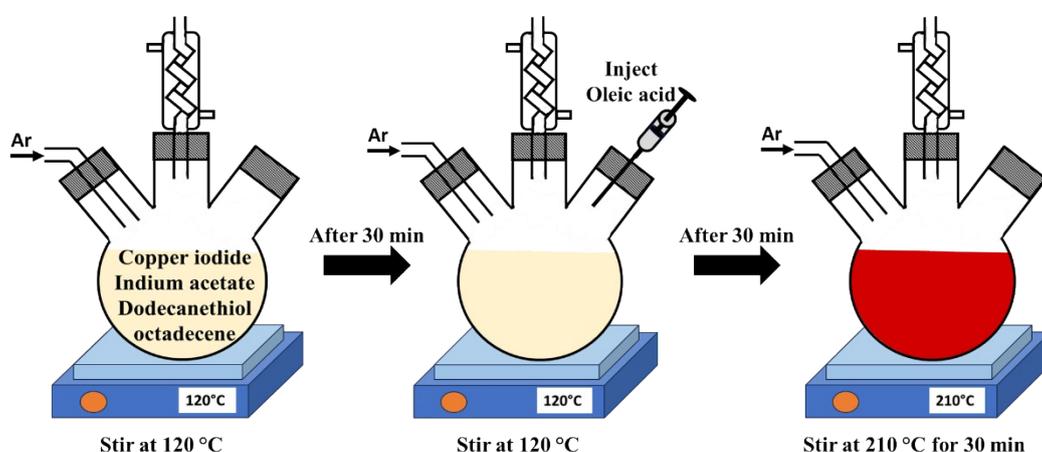


Figure S1: Schematic of CuInS₂ QDs synthesis via hot injection method

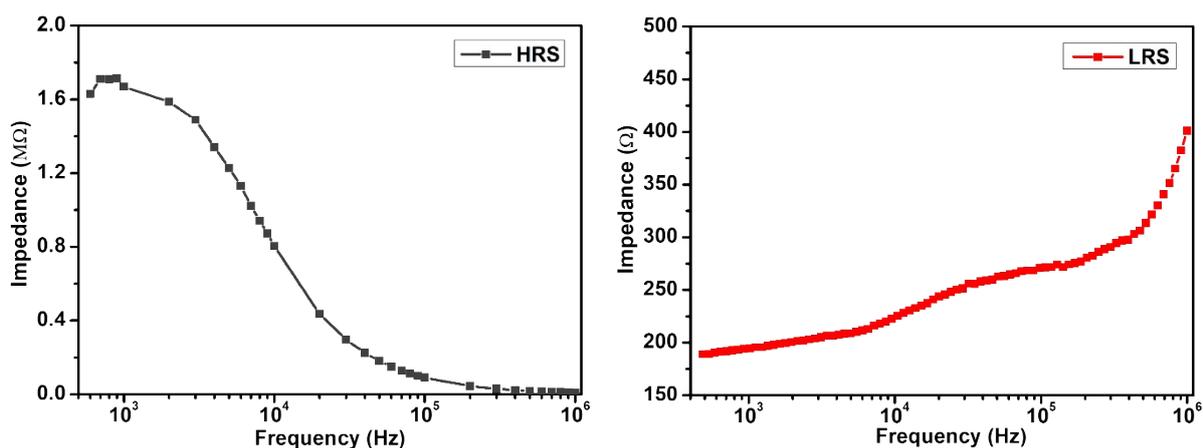


Figure S2: Impedance Z vs frequency characteristic of the device in (a) HRS and (b) LRS